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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): En-Hsing Chen, et al.

Title: NAND MEMORY ARRAY INCORPORATING MULTIPLE SERIES  
SELECTION DEVICES AND METHOD FOR OPERATION OF SAME

Application No.: 10/729,865

Filed:

December 5, 2003

Examiner: Nguyen, Van Thu T.

Group Art Unit:

2824

Atty. Docket No.: 023-0029

Confirmation No.:

8494

March 15, 2005

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COMMISSIONER FOR PATENTS  
P.O. Box 1450  
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**INFORMATION DISCLOSURE STATEMENT**

***37 C.F.R. § 1.97(b)***

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, § 1.97 and § 1.98, the undersigned brings to the Examiner's attention in the above-identified application the patents, publications, applications or other information identified in the attached:

- ☒ Form(s) PTO/SB/08A (5 page(s), with copy of 4 reference(s)).
- ☒ Form(s) PTO/SB/08B (2 page(s), with copy of 20 reference(s)).
- ☒ Listing of Pending Applications (1 page(s), with copy of no application(s)).
- ☐ Other: N/A

Citation of such information shall not be construed as (i) an admission that the information necessarily is, or corresponds to, prior art with respect to the instant invention, (ii) a representation that a search has been made, other than as described herein, or (iii) an admission that the information cited herein is, or is considered to be, material to patentability as defined in § 1.56(b).

For each item of information listed that is not in the English language, the undersigned has provided a concise explanation of the relevance through (i) an English language abstract, (ii) an English language equivalent application, or (iii) if cited in a search report or other action by a foreign patent office in a counterpart foreign application, an English language version of the search report or action that indicates the degree of relevance found by the foreign office.

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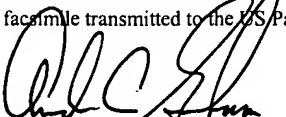
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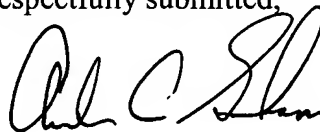
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- ☐ This Information Disclosure Statement is filed within three months of the filing date of a national application other than a continued prosecution application under § 1.53(d) or within three months of entry of the national stage as set forth in § 1.491 in an international application. Therefore, no fee is required.
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 Andrew C. Graham	3-15-05 Date

Respectfully submitted,

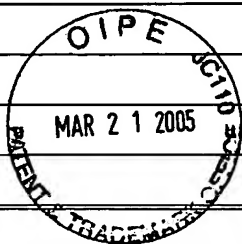


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PTO/SB/08A (Substitute for form 1449/PTO)	Attorney Docket No.: 023-0029
	Application No.: 10/729,865
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	First Named Inventor: En-Hsing Chen et al.
	Filing Date: December 5, 2003
	Group Art Unit: 2824
	Examiner Name: Van Thu Nguyen
	Date Submitted: March 15, 2005

Sheet 1 of 5



U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
	AA	4,142,176	02-27-1979	Dozier		
	AB	4,543,594	09-24-1985	Mohsen et al.		
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	AF	5,301,144	04-05-1994	Kohno		
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	AK	5,621,683	04-15-1997	Young		
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	AN	JA 62-142363	06-25-1987			
	AO	JA 62-155568	07-10-1987			
	AP	JA-2001-358237	12-26-2001			
	AQ	JA-2002-280467	09-27-2002			
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<sup>1</sup>Applicant's unique citation designation number (optional).

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PTO/SB/08A (Substitute for form 1449/PTO)	Attorney Docket No.: 023-0029
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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>	First Named Inventor: En-Hsing Chen et al.
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	AR	5,715,194	02-03-1998	Hu	
	AS	5,751,012	05-12-1998	Wolstenholme et al.	
	AT	5,814,853	09-29-1998	Chen	
	AU	5,835,396	11-10-1998	Zhang	
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	BD	6,185,122 B1	02-06-2001	Johnson et al.	

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	BG					
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	BI	6,188,611 B1	02-13-2001	Endoh et al.	
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	BX					
	BY					
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	BZ	6,515,888	02-04-2003	Johnson et al.	
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	CO					
	CP					
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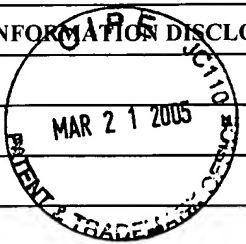
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	CQ	US-2002/0021587 A1.	02-21-2002	Sakui et al	
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	DA	US-5,812,457	09-1998	Arase	
	DB				
	DC				

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### NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Include name of author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	AA	DURISETY, CHANDRA SEKHAR ACHARYULU, "Analysis and Characterization of Single-Poly Floating Gate Devices in 0.35um PDSOI Process", A Thesis Presented for the Master of Science Degree, The University of Tennessee, Knoxville, December 2002, pp. i-viii and 1-80.	
	AB	EVANS, ROBERT J., ET AL., "Energy Consumption Modeling and Optimization for SRAM's," IEEE Journal of Solid-State Circuits, Vol. 30, No. 5, May 1995, pp. 571-579.	
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	AJ	LIN, HORNG-CHIH, ET AL., "Ambipolar Schottky-Barrier TFTs," IEEE Transactions on Electron Devices, Vol. 49, No. 2, February 2002, pp. 264-270.	
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	AL	NISHIHARA, TOSHIYUKI, ET AL., "A Quasi-Matrix Ferroelectric Memory for Future Silicon Storage," IEEE Journal of Solid-State Circuits, Vol. 37, No. 11, November 2002, pp. 1479-1484.	
	AM	PARK, KI-TAE, "Recent Non-Volatile Memory Device & Circuit Technology," Halo LSI Inc, (date unknown), 35 pages.	
	AN	ROIZIN, YAKOV, ET AL., "Plasma-Induced Charging in Two Bit per Cell SONOS Memories," Tower Semiconductor Ltd., Migdal HaEmek 23105, Israel, (date unknown), 4 pages.	
Examiner Signature		Date Considered	

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Examiner Initials*	Cite No. <sup>1</sup>	Include name of author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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	AP	STURM, J. C., ET AL., "Leakage Current Modeling of Series-Connected Thin Film Transistors," IEEE Transactions on Electron Devices, Vol. 42, No. 8, August 1995, pp. 1561-1563.	
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	AT	THEAN, AARON, ET AL., "Flash memory: towards single-electronics," IEEE Potentials, October/November 2002, pp. 35-41.	
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